

10/507920

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/507920	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 10:05
L2	34	MEMS and (sacrificial adj layer adj2 made adj2 silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 10:18
L3	2	("7083997").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 10:18
L4	2	3 and (silicon or sacrificial or layer or plasma or etch or etching or fluorine or chemistry or MEMS or XeF or metal or gate or BrF or surface or micromachine or characterized or xenon or difluoride or bromine or trifluoride or gold or titanium or copper or platinum or tungsten air or gap or insulator or substrate or membrane)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:02
L5	2	("6538296").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:01
L6	2	("6422077").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:01
L7	2	("6440767").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:02

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L8	2	7 and (silicon or sacrificial or layer or plasma or etch or etching or fluorine or chemistry or MEMS or XeF or metal or gate or BrF or surface or micromachine or characterized or xenon or difluoride or bromine or trifluoride or gold or titanium or copper or platinum or tungsten air or gap or insulator or substrate or membrane)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:08
L9	2	("6331257").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:08
L10	2	9 and (silicon or sacrificial or layer or plasma or etch or etching or fluorine or chemistry or MEMS or XeF or metal or gate or BrF or surface or micromachine or characterized or xenon or difluoride or bromine or trifluoride or gold or titanium or copper or platinum or tungsten air or gap or insulator or substrate or membrane)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:11
L11	2	("6046659").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:11
L12	2	11 and (silicon or sacrificial or layer or plasma or etch or etching or fluorine or chemistry or MEMS or XeF or metal or gate or BrF or surface or micromachine or characterized or xenon or difluoride or bromine or trifluoride or gold or titanium or copper or platinum or tungsten air or gap or insulator or substrate or membrane)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/08 11:11